

N-Channel Power MOSFET

800V, 4A, 3.0Ω

FEATURES

- Low R_{DS(ON)} 3Ω (Max.)
- Low gate charge typical @ 20nC (Typ.)

TO-220

• Improve dV/dt capability

| KEY PERFORMANCE PARAMETERS | | | | |
|-----------------------------------|------------|----|--|--|
| PARAMETER | VALUE UNIT | | | |
| V _{DS} | 800 | V | | |
| R _{DS(on)} (max) | 3.0 | Ω | | |
| Qg | 20 | nC | | |



- Power Supply
- Lighting



| ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted) | | | | | |
|---|-------------------|---------------|---------|------|--|
| PARAMETER | SYMBOL | TO-220 | ITO-220 | UNIT | |
| Drain-Source Voltage | V _{DS} | 800 | | V | |
| Gate-Source Voltage | V _{GS} | ±30 | | V | |
| Continuous Drain Current (Note 4) $T_{\rm C} = 25^{\circ}{\rm C}$ | | 4 | | A | |
| $T_{\rm C} = 100^{\circ}{\rm C}$ | Ι _D | 2.5 | | | |
| Pulsed Drain Current (Note 2) | I _{DM} | 16 | | А | |
| Total Power Dissipation @ $T_c = 25^{\circ}C$ | P _{DTOT} | 123 | 38.7 | W | |
| Single Pulsed Avalanche Energy (Note 3) | E _{AS} | 7 | 6 | mJ | |
| Single Pulsed Avalanche Current (Note 3) | I _{AS} | 4 | 4 | А | |
| Repetitive Avalanche Energy | E _{AR} | 12 | 2.3 | mJ | |
| Peak Diode Recovery ^(Note 7) | dV/dt | 4 | .5 | V | |
| Operating Junction and Storage Temperature Range | T_J,T_STG | - 55 to | o +150 | °C | |

| THERMAL PERFORMANCE | | | | | |
|--|-----------------|---------------|---------|------|--|
| PARAMETER | SYMBOL | TO-220 | ITO-220 | UNIT | |
| Junction to Case Thermal Resistance | $R_{\Theta JC}$ | 1.01 | 3.23 | °C/W | |
| Junction to Ambient Thermal Resistance | $R_{\Theta JA}$ | 62.5 | | °C/W | |

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.



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| ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted) | | | | | | |
|---|--|------------------------|-----|-----|----------|------|
| PARAMETER | CONDITIONS | SYMBOL | MIN | ТҮР | MAX | UNIT |
| Static (Note 4) | | | | | | |
| Drain-Source Breakdown Voltage | $V_{GS} = 0V, I_D = 250\mu A$ | BV _{DSS} | 800 | | | V |
| Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | V _{GS(TH)} | 2.0 | | 4.0 | V |
| Gate Body Leakage | $V_{GS} = \pm 30V, V_{DS} = 0V$ | I _{GSS} | | | ±100 | nA |
| Zero Gate Voltage Drain Current | $V_{DS} = 700 V, V_{GS} = 0 V$ | I _{DSS} | | 🔺 | 10 | μA |
| Drain-Source On-State Resistance | $V_{GS} = 10V, I_D = 1.2A$ | R _{DS(on)} | | 2.5 | 3.0 | Ω |
| Forward Transconductance | $V_{DS} = 30V, I_{D} = 1.2A$ | g _{fs} | | 7.1 | _ | S |
| Dynamic ^(Note 5) | | | | | | |
| Total Gate Charge | | Qg | (| 20 | | |
| Gate-Source Charge | $V_{DS} = 640V, I_D = 4.0A,$ $V_{GS} = 10V$ | Q _{gs} | | 3.7 | | nC |
| Gate-Drain Charge | | Q _{gd} | -7 | 8.2 | | |
| Input Capacitance | $V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz | C _{iss} | | 955 | | |
| Output Capacitance | | C _{oss} | | 80 | | pF |
| Reverse Transfer Capacitance | | C _{rss} | | 13 | | |
| Gate Resistance | F = 1MHz, open drain | Rg | | | 3 | Ω |
| Switching (Note 6) | | | | | | |
| Turn-On Delay Time | | t _{d(on)} | | 49 | | |
| Turn-On Rise Time | $V_{DD} = 400V,$ | t _r | | 38 | | |
| Turn-Off Delay Time | R _{GEN} = 25Ω, I _D = 4.0A, V _{GS} = 10V, | t _{d(off)} | | 146 | | ns |
| Turn-Off Fall Time | | t _f | | 50 | | |
| Source-Drain Diode (Note 4) | | | | | | |
| Forward On Voltage | I _S = 4.0A, V _{GS} = 0V | V _{SD} | | | 1.5 | V |
| Reverse Recovery Time | $V_{GS} = 0V, I_{S} = 4A$ | t _{rr} | | 487 | | ns |
| Reverse Recovery Charge | dl _F /dt = 100A/µs | Q _{rr} | | 2.8 | | μC |

Notes:

1. Current limited by package

2. Pulse width limited by the maximum junction temperature

- 3. L = 10mH, I_{AS} = 4.0A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25^oC
- 4. Pulse test: $PW \le 300\mu s$, duty cycle $\le 2\%$
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.
- 7. $I_{SD} \le 8A$, dI/dt $\le 200A/uS$, Vdd $\le BV_{DSS}$, Starting $T_J = 25^{\circ}C$.



ORDERING INFORMATION

| PART NO. | PACKAGE | PACKING |
|---------------|---------|--------------|
| TSM4N80CZ C0G | TO-220 | 50pcs / Tube |
| TSM4N80CI C0G | ITO-220 | 50pcs / Tube |

Note:

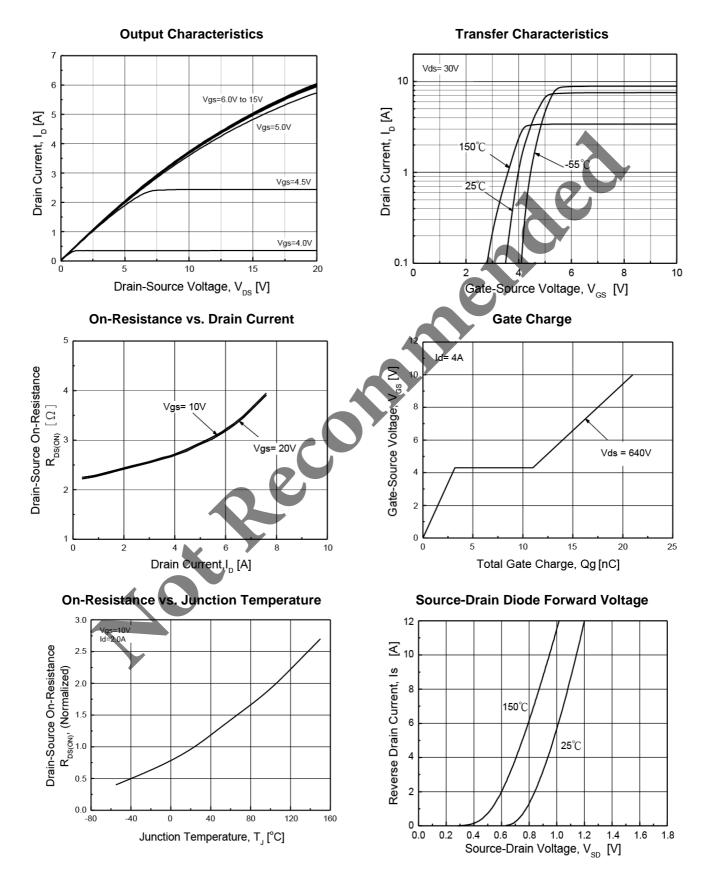
the company of the contract Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC 1.

2. Halogen-free according to IEC 61249-2-21 definition



CHARACTERISTICS CURVES

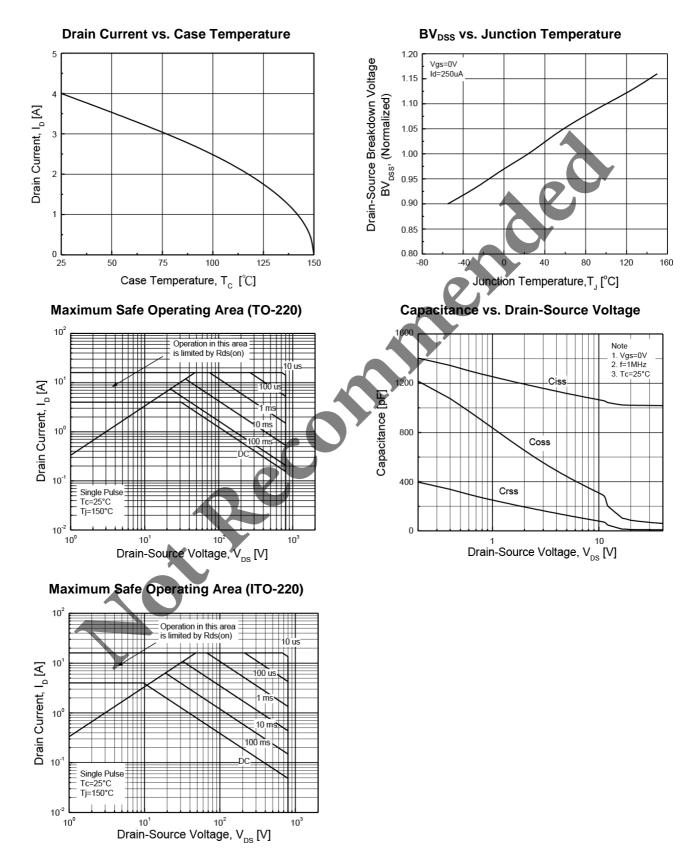
 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$





CHARACTERISTICS CURVES

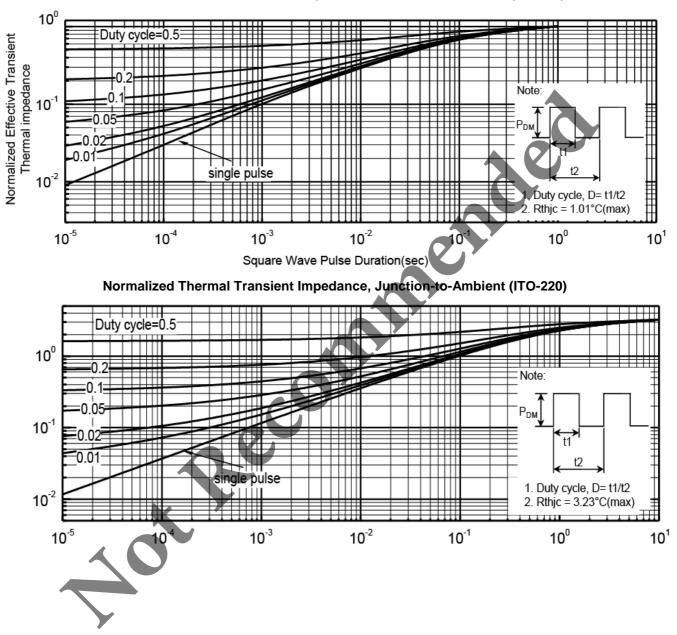
 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$





CHARACTERISTICS CURVES

 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$



Normalized Thermal Transient Impedance, Junction-to-Ambient (TO-220)

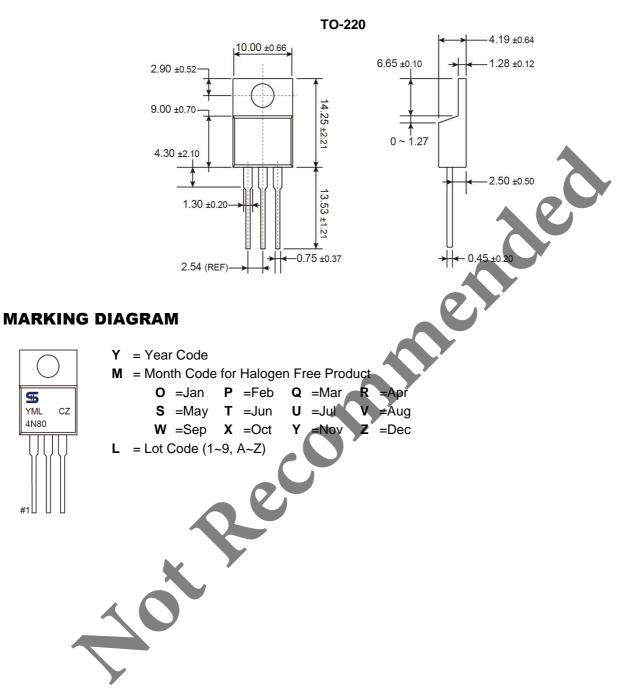




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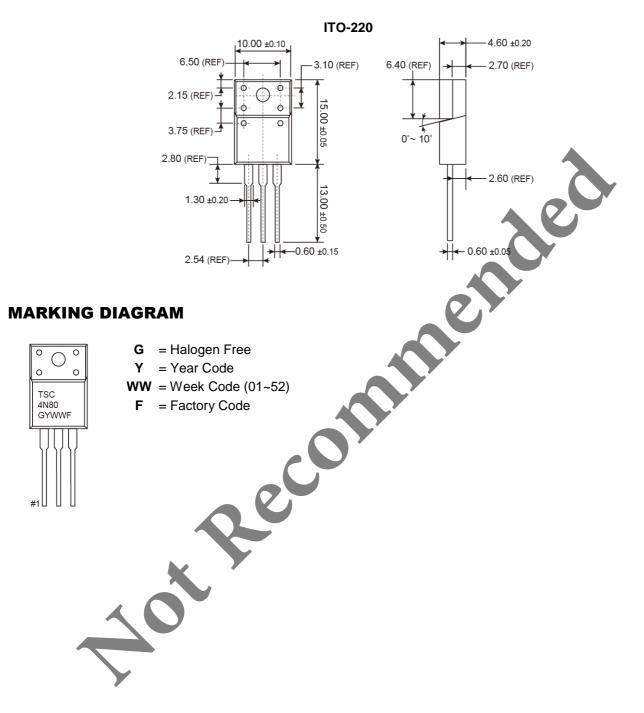




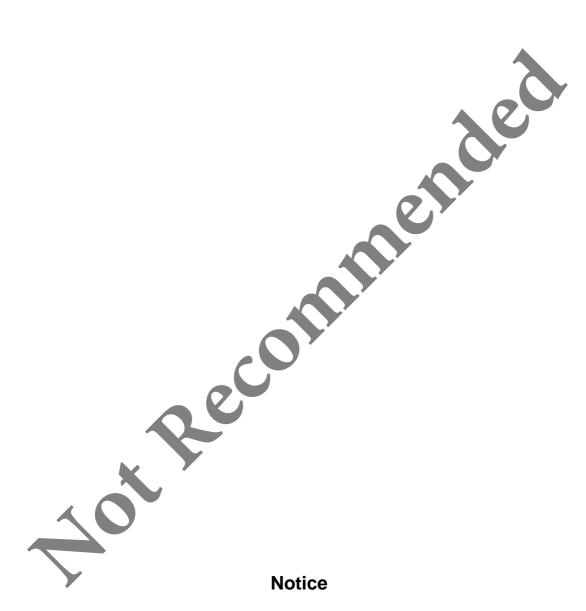


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PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)







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